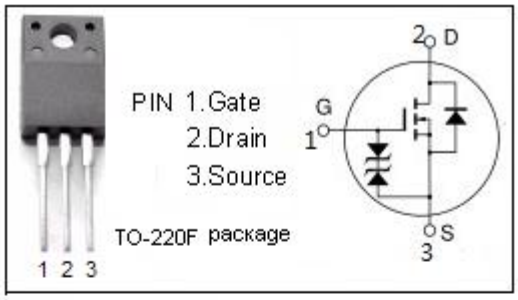
isc N-Channel MOSFET Transistor 2SK2350

DESCRIPTION

- Drain Current I_D= 8.5A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 200V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

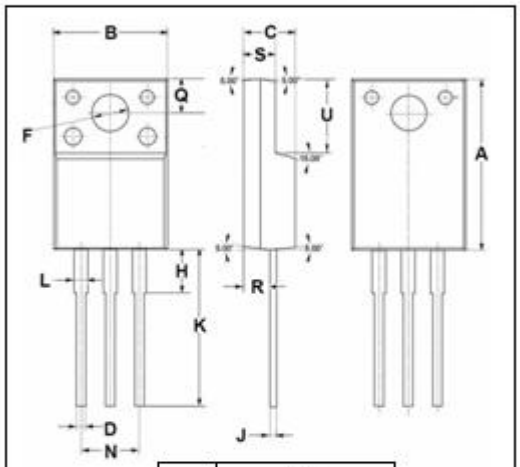
- Switching Regulators
- DC-DC Converter,
- Motor Control

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	200	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	8.5	A
$I_{D(puls)}$	Pulsed Drain Current	34	A
P_{tot}	Total Dissipation@TC=25℃	30	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	4.16	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

isc N-Channel Mosfet Transistor 2SK2350

• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 10mA	200			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D=1mA	1.5		3.5	V
V_{SD}	Diode Forward On-Voltage	I_S=10A ;V_{GS}= 0			2.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 5A		0.26	0.4	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±16V;V_{DS}= 0			±10	μA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 200V; V_{GS}= 0			100	μA
C_{iss}	Input Capacitance	V_{DS}=10V; V_{GS}=0V; f_T=1MHz		700		pF
C_{rss}	Reverse Transfer Capacitance			80		
C_{oss}	Output Capacitance			270		
t_r	Rise Time	V_{GS}=10V; I_D=5A; V_{DD}=100V; R_L=20 Ω		15		ns
t_{on}	Turn-on Time			25		
t_f	Fall Time			15		
t_{off}	Turn-off Time			70		